

Vincent P Labella

List of Publications by Year in descending order

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17
papers

135
citations

1307594

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1199594

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times ranked

178
citing authors

#	ARTICLE	IF	CITATIONS
1	Schottky barrier height measurements of Cu/Si(001), Ag/Si(001), and Au/Si(001) interfaces utilizing ballistic electron emission microscopy and ballistic hole emission microscopy. AIP Advances, 2013, 3, .	1.3	31
2	Fabrication of 5-20 nm thick HfO_2 -W films. AIP Advances, 2014, 4, .	1.3	21
3	Time dependent changes in Schottky barrier mapping of the W/Si(001) interface utilizing ballistic electron emission microscopy. Journal of Applied Physics, 2015, 117, .	2.5	12
4	Nanoscale mapping of the W/Si(001) Schottky barrier. Journal of Applied Physics, 2014, 116, 023705.	2.5	9
5	Signatures of the semiconductor crystallographic orientation on the charge transport across non-epitaxial diodes. Applied Physics Letters, 2012, 100, .	3.3	8
6	Temperature dependent spin precession measurements in trilayer graphene utilizing co/graphene contacts. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 03D115.	1.2	8
7	Characterization of metal oxide layers grown on CVD graphene. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	7
8	Relating spatially resolved maps of the Schottky barrier height to metal/semiconductor interface composition. Journal of Applied Physics, 2016, 119, .	2.5	7
9	Nanoscale Schottky barrier mapping of thermally evaporated and sputter deposited W/Si(001) diodes using ballistic electron emission microscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	6
10	Detection of silicide formation in nanoscale visualization of interface electrostatics. Applied Physics Letters, 2017, 110, 141606.	3.3	6
11	Fabrication of an electrical spin transport device utilizing a diazonium salt/hafnium oxide interface layer on epitaxial graphene grown on $6\text{H-SiC}(0001)$. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 04E109.	1.2	5
12	Pulsed-N ₂ assisted growth of 5-20 nm thick HfO_2 -W films. AIP Advances, 2015, 5, .	1.3	4
13	Schottky barrier and attenuation length for hot hole injection in nonepitaxial Au on p-type GaAs. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 04E110.	1.2	3
14	Microstructure fabrication process induced modulations in CVD graphene. AIP Advances, 2014, 4, 127143.	1.3	3
15	Nanoscale Schottky barrier visualization utilizing computational modeling and ballistic electron emission microscopy. Journal of Applied Physics, 2018, 123, .	2.5	3
16	Visualizing metal/HfO ₂ /SiO ₂ /Si(001) interface electrostatic barrier heights with ballistic hole emission microscopy. Journal of Applied Physics, 2019, 126, 195302.	2.5	1
17	Determination of the energetic resolution of Schottky barrier visualization via interface band structure and parallel momentum conservation. AIP Advances, 2021, 11, .	1.3	1